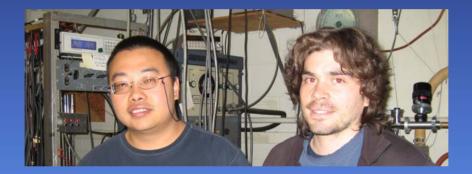
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High-field ground state of graphene at Dirac Point

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- **1. Ground state of Dirac point in high fields**
- 2. Thermopower at Dirac point



Zero-energy mode, *n*=0 Landau Level

For valley K

$$H = \mathbf{v} \begin{bmatrix} 0 & \pi_x + i\pi_y \\ \pi_x - i\pi_y & 0 \end{bmatrix} = \frac{\sqrt{2}\mathbf{v}}{\ell_B} \begin{bmatrix} 0 & a \\ a^+ & 0 \end{bmatrix}$$
$$(\pi_x + i\pi_y)\ell_y$$

$$\boldsymbol{\pi} = \mathbf{k} - e \mathbf{A}$$
 $a = \frac{(\pi_x + i\pi_y)\ell_B}{\sqrt{2}}$



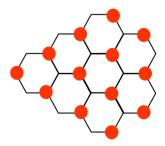
$$H^2 \Psi_n = E_n^2 \Psi_n$$

$$E_n = \sqrt{2n} \frac{\mathbf{v}}{\ell_B} \qquad \Psi_n = \begin{bmatrix} |n-1\rangle \\ |n\rangle \end{bmatrix}$$

$$\Psi_0 = \begin{bmatrix} 0 \\ |0\rangle \end{bmatrix}$$

For *n*=0 Landau Level

K-K' valley index same as *A-B* sublattice index
 Electrons on *B* sites only



Coulomb interaction energy in high-field state

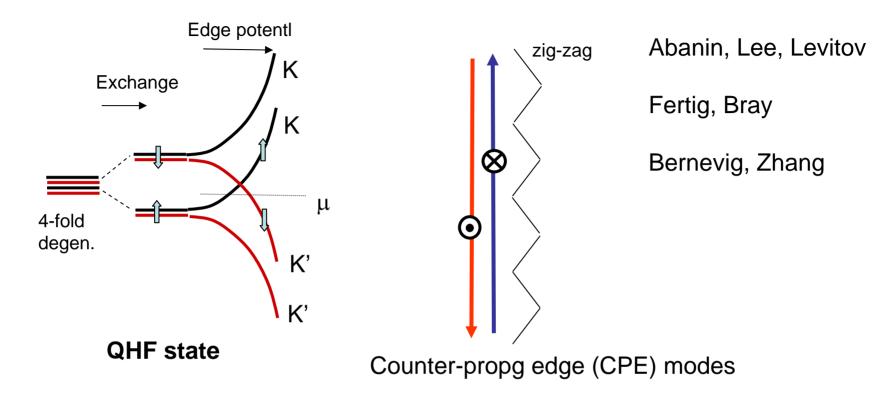
Nomura, MacDonald, PRL 06 Goerbig, Moessner, Doucot, PRB 06 Kun Yang, Das Sarma, MacDonald, PRB 06 Ezawa, JPSJ 06

Abanin, Lee, Levitov, PRL 06, 07 Fertig, Bray, PRL 06 Shimshoni, Fertig, Pai, 08

Alicea, Fisher, PRB 06

Gusynin, Miransky, Sharapov, Shovkovy, PRB 06 Khveshchenko, PRL 02

Quantum Hall Ferromagnet and CPE modes

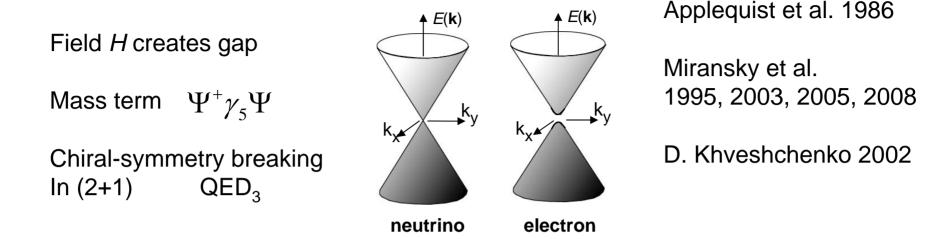


At Dirac point, CPE modes protected

 $R_{xx} \sim 2(h/e^2)$ at intense fields (dissipative to very large H)

Realization of quantized spin-Hall system

Magnetic Catalysis (field induced gap)

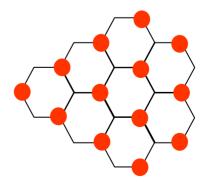


Field-enhancement of DOS at Dirac Point Exciton condensation of electron hole pairs

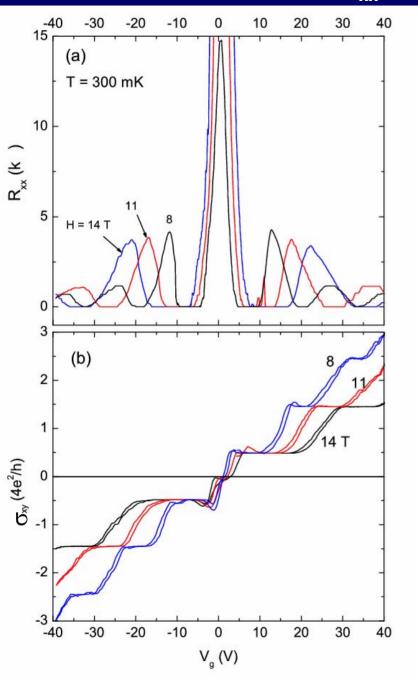
Order parameter for $H > H_c$

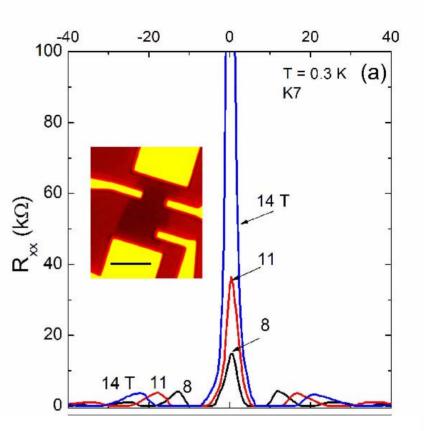
$$\left\langle \overline{\Psi}\Psi\right\rangle = \sum_{\sigma} \left|\psi_{A\sigma}\right|^2 - \left|\psi_{B\sigma}\right|^2$$

Equivalent to sublattice CDW



The resistance R_{xx} and Hall conductivity in graphene

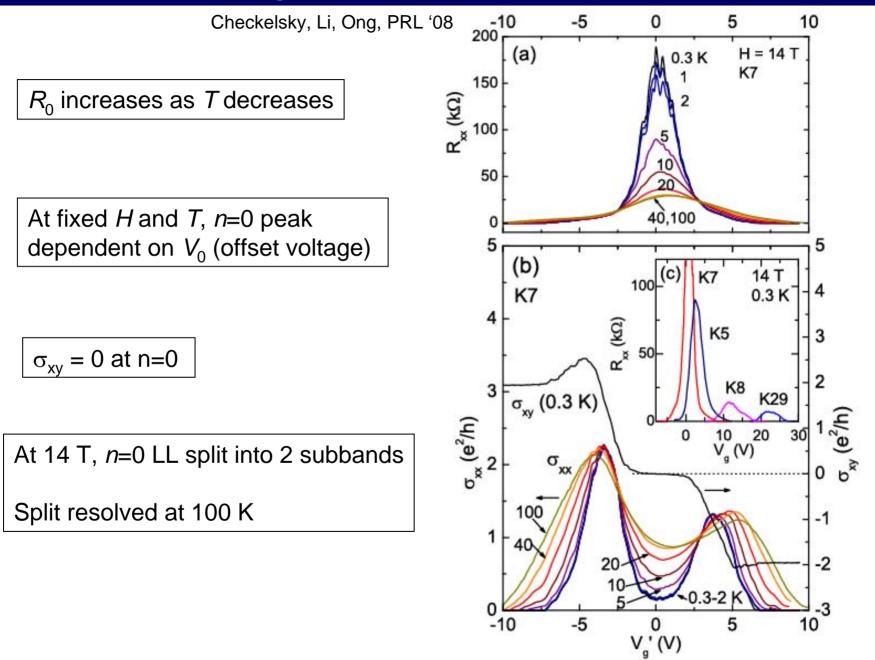




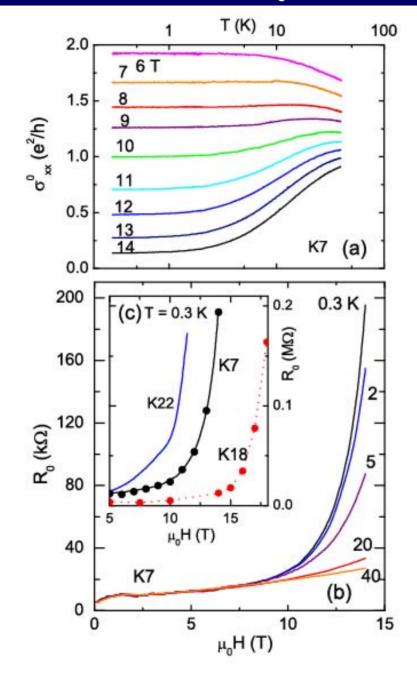
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R_{xx} diverges with H at Dirac Point

Divergent R0 and zero-Hall step



R₀ saturates below 2 K

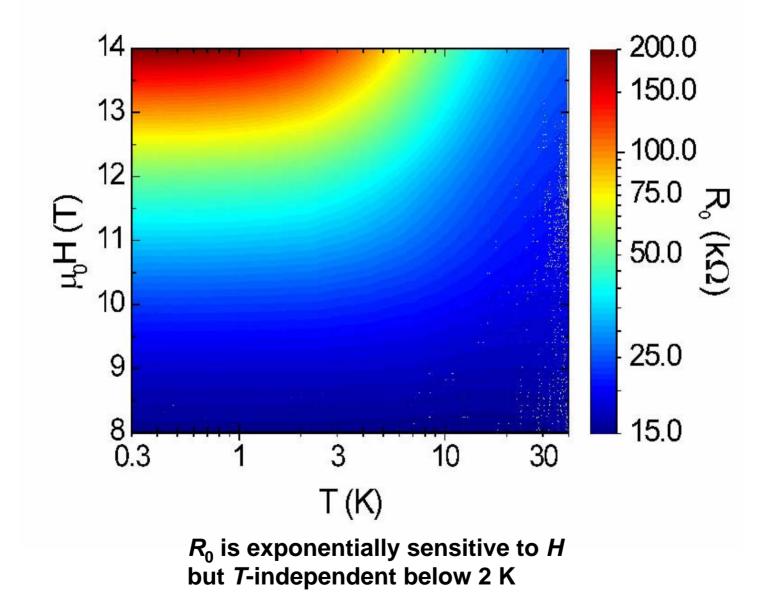


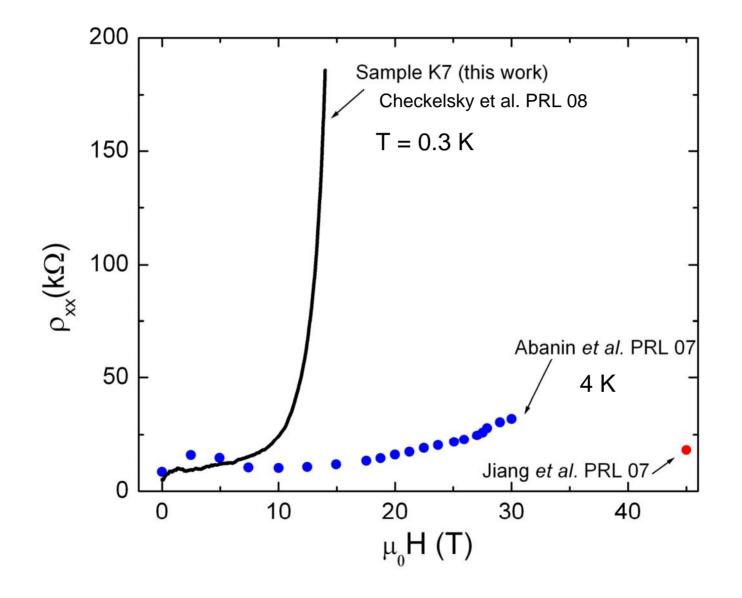
Conductance saturates T below 2 K

Divergence in R_0 steepest At 0.3 K

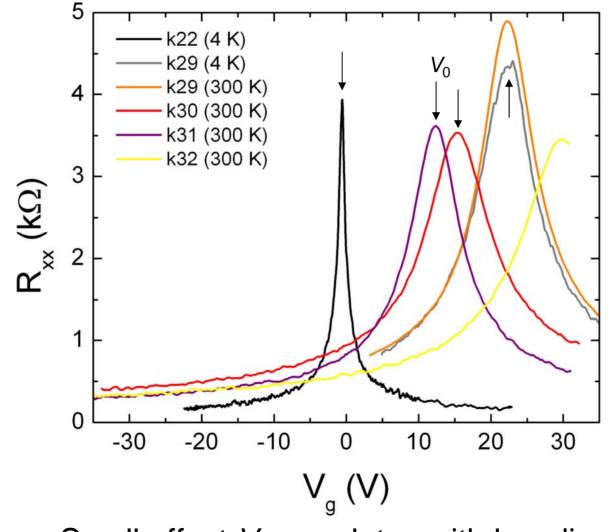
Sample dependent

Contour map of R_0 at Dirac point in *H*-*T* plane





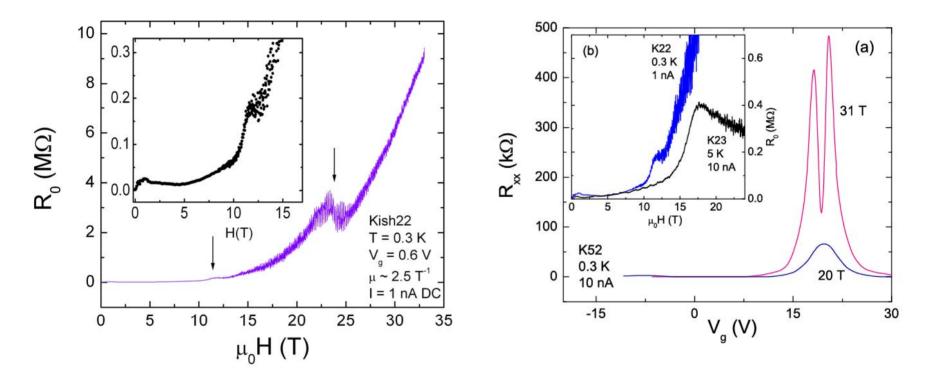
Offset Gate voltage V_0 -- an important parameter



Small offset V_0 correlates with low disorder

Spurious features from self-heating

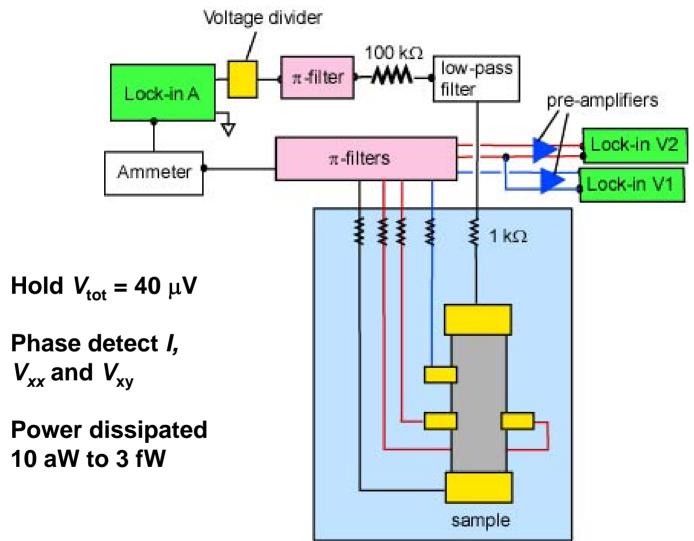
Power dissip P > 10 pW leads to thermal runaway at Dirac point

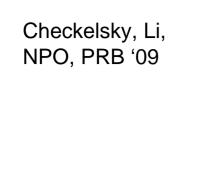


A major experimental obstacle

Adopt ultralow dissipation measurement circuit

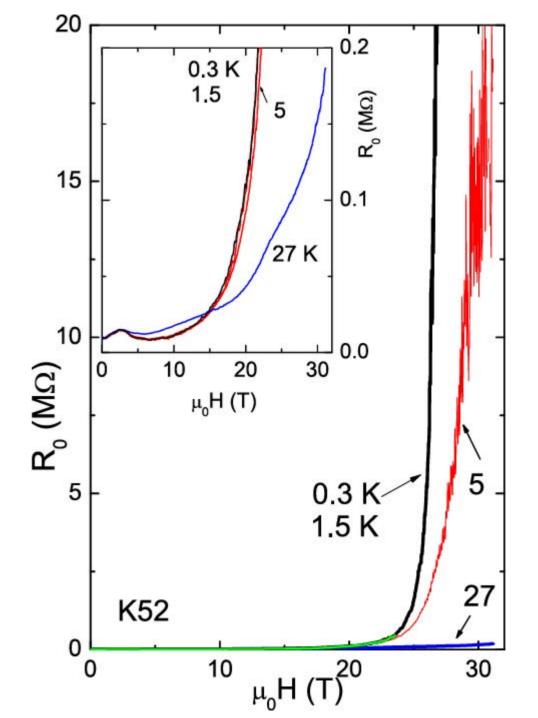
Checkelsky, Li, NPO, PRB '09



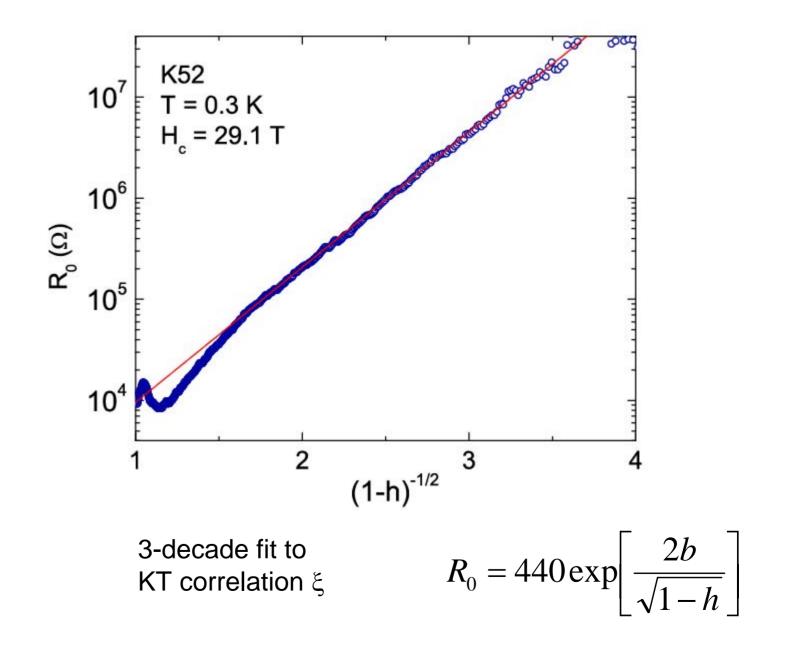


At 0.3 K, R_0 diverges to 40 M Ω

Divergence in *R*₀ seems *singular*



Fits to Kosterlitz-Thouless correlation length over 3 decades



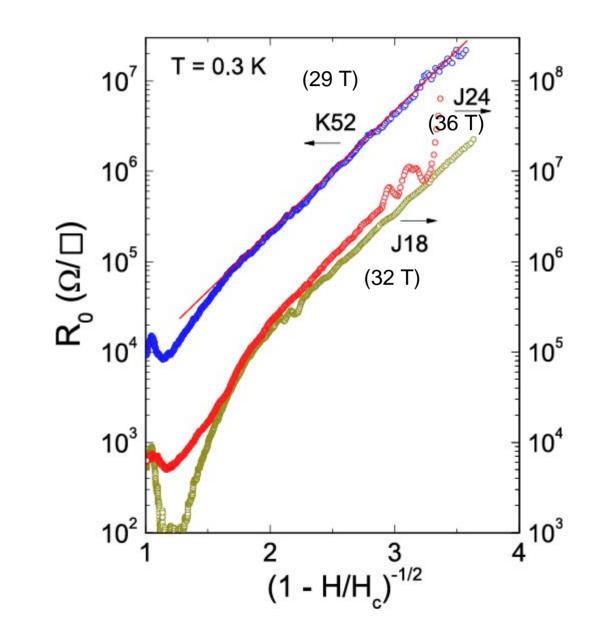
Kosterlitz Thouless fit in Samples K52, J18 and J24

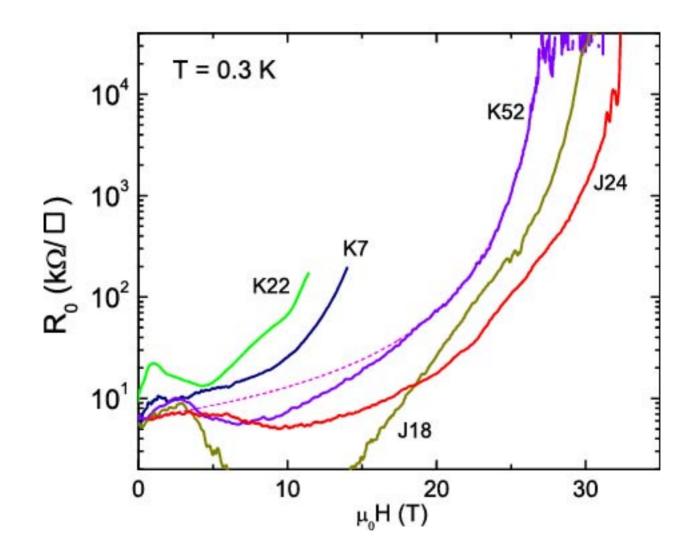
Checkelsky, Li, NPO, PRB '09

$$R_0 = A \exp\left[\frac{2b}{\sqrt{1-h}}\right]$$

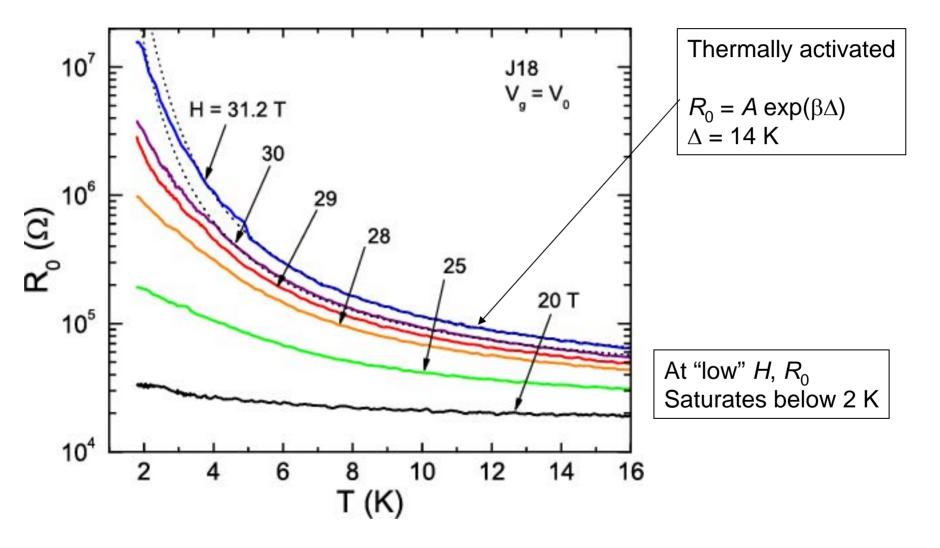
Slopes b are similar

 $H_{\rm c}$ sample dependt

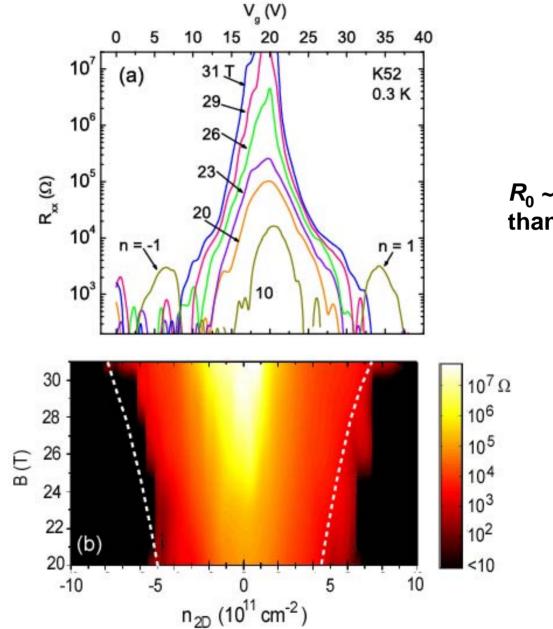


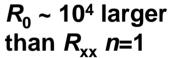


Checkelsky, Li, NPO, PRB '09



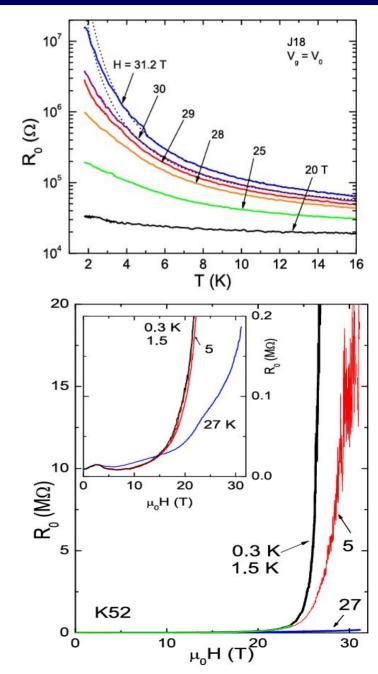
Divergence confined to n = 0 LL



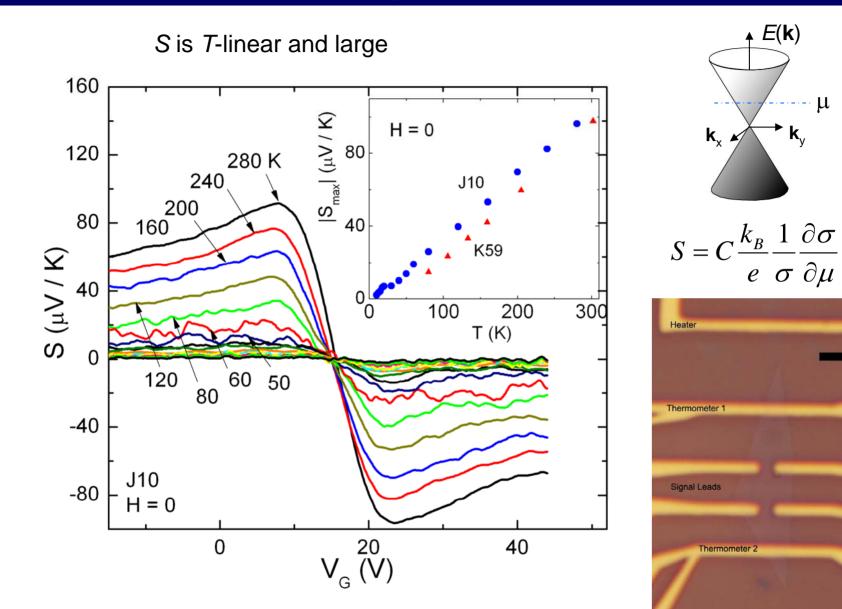


Phase diagram in *T-H* plane at Dirac point

Constant-R₀ contours Η activated $H_{\rm c}$ saturates KT like Т



Thermopower in zero field

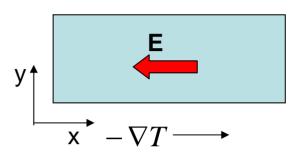


Current response

$$\mathbf{J} = \vec{\boldsymbol{\alpha}} \cdot (-\vec{\nabla}T)$$

Measured E field

$$E_i = S_{ij} (-\partial_j T)$$



Total charge current is zero (open boundaries)

$$J_{i} = \sigma_{ij}E_{j} + \alpha_{ij}(-\partial_{j}T)$$

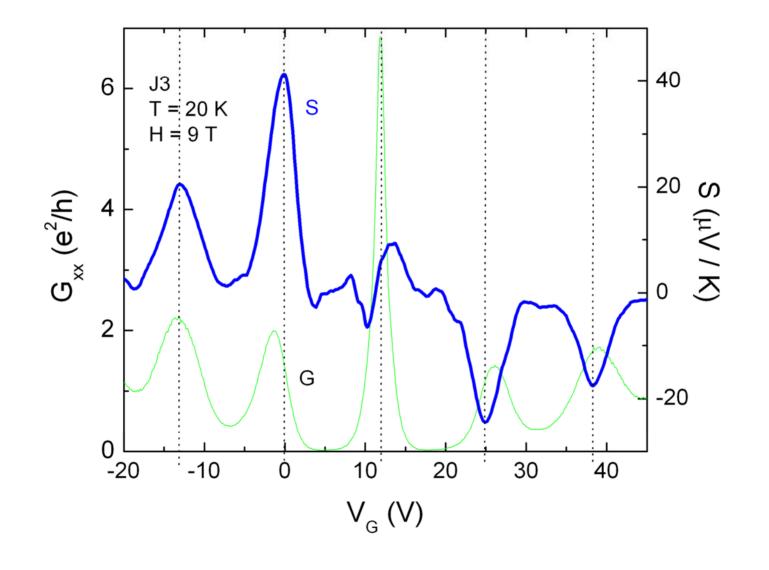
$$S = -S_{xx} = (\rho\alpha + \rho_{yx}\alpha_{xy}) \quad \text{(thermopower)}$$

$$S_{yx} = \rho\alpha_{xy} - \alpha\rho_{yx} \quad \text{(Nernst effect)}$$

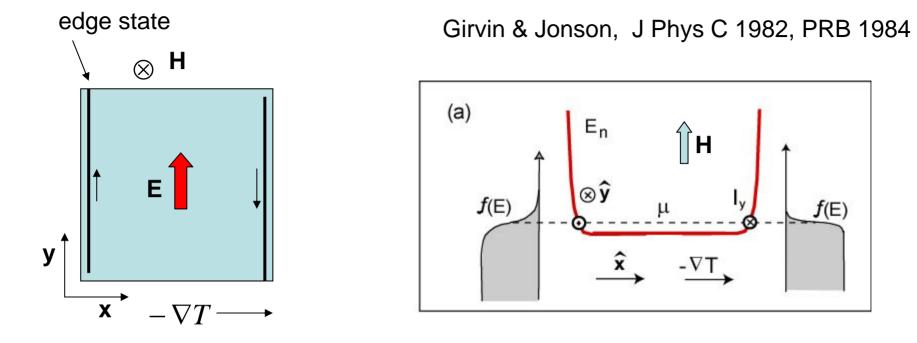
Can invert to find α_{ij}

$$\alpha = -(\sigma E_x + \sigma_{xy} E_y) / |\partial T|$$
$$\alpha_{xy} = (\sigma_{yx} E_x + \sigma E_y) / |\partial T|$$

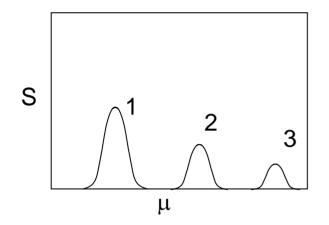
Thermopower at 9 T and 20 K



Thermopower in QHE regime (n>0)

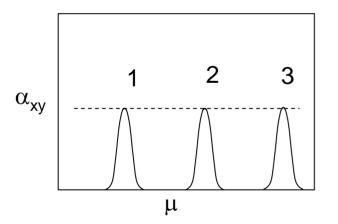


$$I_{x} = 0 \qquad I_{y} = \frac{L}{2\pi} \sum_{n} \int dk \frac{e}{\hbar L} \hbar v_{k} f(\varepsilon_{nk})$$
$$\alpha_{xy} = \frac{e}{\hbar T} \sum_{n} \int_{E_{n}}^{\infty} d\varepsilon (\varepsilon - \mu) \left(-\frac{\partial f}{\partial \varepsilon}\right)$$



1) Current response to ΔT is off-diagonal

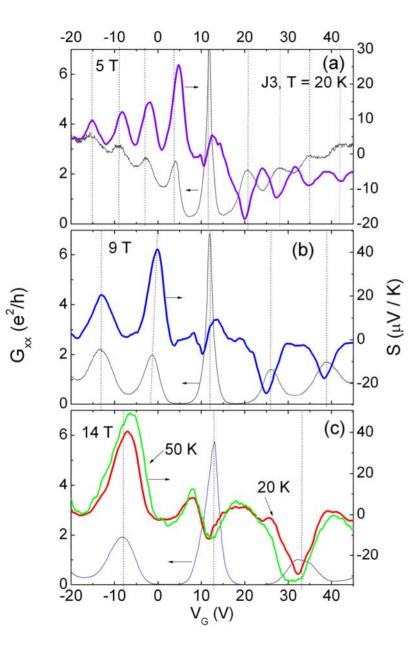
$$S = \rho_{yx} \alpha_{xy} \qquad S_{\max}(n) = \frac{k_B \ln 2}{e(n + \frac{1}{2})}$$



 α_{xy} is quantized indpt of *n*

$$\alpha_{xy} = \frac{k_B e}{h} \ln 2 = 93 \text{ nA/K}$$

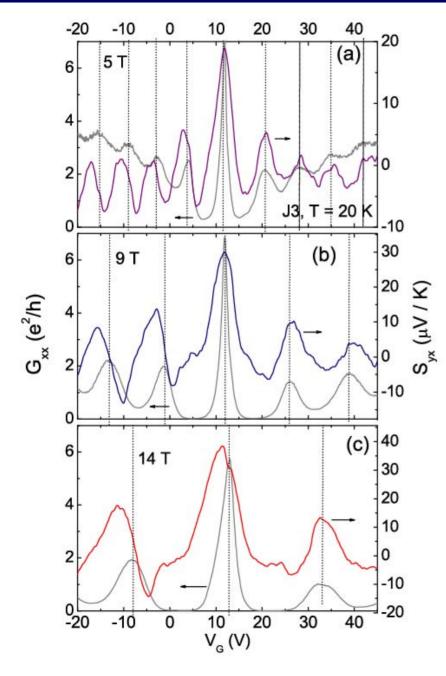
Thermopower at 5, 9 and 14 T



Features of thermopower

- 1. Charge antisymmetric
- 2. Peak at n=1 nearly indpt of H
- 3. Very weak T dependence below 50 K

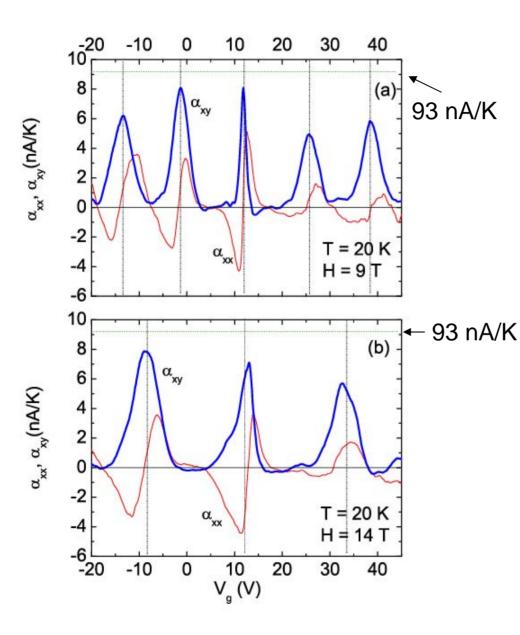
Nernst Signal (off-diagonal S_{yx})



Nernst signal in graphene

- Charge symmetric
- Nernst signal is anomalously large at Dirac Point
- 3. Peaks at n=0, but dispersive for n=1,2,3...
- At n=0, sign is positive (similar to vortex-Nernst signal in superconductors)

The thermoelectric tensor elements αxx and αxy



$$\alpha = -(\sigma E_x + \sigma_{xy} E_y) / |\partial T|$$

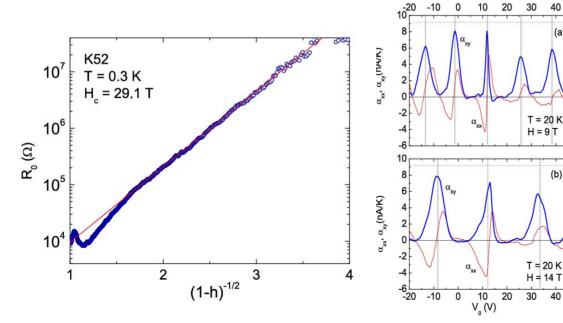
$$\alpha_{xy} = (\sigma_{yx} E_x + \sigma E_y) / |\partial T|$$

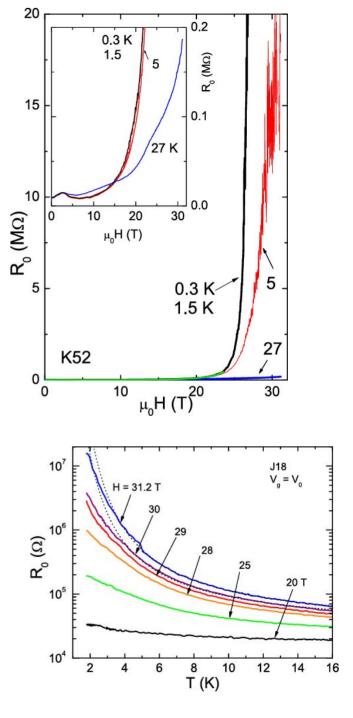
- 1) Peaks well defined
- 2) α_{xx} is antisym. In e
- 3) α_{xy} is symmetric
- 4) A surprise:
- α_{xy} peak very narrow at *n*=0

Within 20% of quantized value (need to estimate gradient more accurately)

In graphene

- 1. Field induces transition to insulating state at $H_{\rm c}$ that correlates with V_{0} .
- 2. For $H > H_c$, R_0 is thermally activated ($\Delta \sim 14$ K), H<Hc, R0 saturates below 2 K.
- 3. $H < H_c$, divergence fits KT form exp[2b/(h-1)^{1/2}].
- 4. Large Nernst signal at Dirac point.
- 5. α_{xy} consistent with quantization ~ 90 nA/K indpt of T, H and n.





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(b)

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